

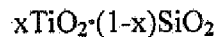
AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A titanosilicate represented by the following compositional formula (1), wherein in the infrared absorption spectrum measured in the dehydrated state, the absorption spectrum has an absorption band having a relative maximum value at $930 \pm 15 \text{ cm}^{-1}$:

Compositional Formula (1)



(wherein x is from 0.0001 to 0.2), and

wherein in the infrared absorption spectrum measured in the dehydrated state, the greatest value in the region of $900\text{-}950 \text{ cm}^{-1}$ of the absorption spectrum is present in the region of $930 \pm 15 \text{ cm}^{-1}$.

2. (canceled).

3. (currently amended): The titanosilicate according to claim 21, wherein in the infrared absorption spectrum measured in the dehydrated state, the greatest value in the region of $900\text{-}950 \text{ cm}^{-1}$ of the absorption spectrum is present in the region of $930 \pm 10 \text{ cm}^{-1}$.

4. (currently amended) The titanosilicate according to ~~any one of claims 1-3~~claim 1, wherein in the infrared absorption spectrum measured in the dehydrated state, the absorption

spectrum has an absorption band having a relative maximum value at $1010 \pm 15 \text{ cm}^{-1}$ in addition to $930 \pm 15 \text{ cm}^{-1}$.

5. (currently amended): The titanosilicate according to claim 1 ~~any one of claims 1-4~~, wherein in the infrared absorption spectrum measured in the dehydrated state, the absorption spectrum has an absorption band having a relative maximum value at $865 \pm 15 \text{ cm}^{-1}$ in addition to $930 \pm 15 \text{ cm}^{-1}$.

6. (currently amended): The titanosilicate according to claim 1 ~~any one of claims 1-5~~, which is a crystalline titanosilicate having a structure code MWW characterized by the powder X-ray diffraction pattern shown in Table 7:

[Table 7]

Table 7: Powder X-Ray Diffraction Lines provided by MWW Structure

d/Å	Relative Intensity (s: strong, m: medium, w: weak)
12.3 ± 0.6	s
11.0 ± 0.6	s
8.8 ± 0.5	s
6.2 ± 0.4	m
5.5 ± 0.3	w
3.9 ± 0.2	m
3.7 ± 0.2	w
3.4 ± 0.2	s

(in the above Table, "d/Å" means that the unit of the lattice spacing d is Angstrom.)

7. (currently amended): The titanosilicate according to claim 1 ~~any one of claim 1 to 7~~, wherein x is from 0.001 to 0.2.

8. (currently amended): A process for producing the titanosilicate described in claim 1 ~~any one of claims 1 to 7~~, comprising the following first to fourth steps:

First Step:

a step of heating a mixture containing a template compound, a boron-containing compound, a silicon-containing compound and water to obtain a precursor (A);

Second Step:

a step of acid-treating the precursor (A) obtained in the first step;

Third Step:

a step of heating the acid-treated precursor (A) obtained in the second step together with a mixture containing a template compound, a titanium-containing compound and water to obtain a precursor (B); and

Fourth Step:

a step of calcining the precursor (B) obtained in the third step to obtain the titanosilicate.

9. (original): The process for producing the titanosilicate according to claim 8, wherein the following first-2 step is performed between the first step and the second step and the substance obtained in the first-2 step is used instead of the precursor (A) in the second step:

First-2 Step:

a step of calcining a part or entirety of the precursor (A) obtained in the first step.

10. (currently amended): The process for producing the titanosilicate according to claim ~~8 or 9~~, wherein the following third-2 step is performed between the third step and the fourth step and the substance obtained in the third-2 step is used instead of the precursor (B) in the fourth step:

Third-2 Step:

a step of acid-treating a part or entirety of the precursor (B) obtained in the third step.

11. (currently amended): The process for producing the titanosilicate according to claim 8 ~~any one of claims 8-10~~, wherein the following third-3 step is performed between the third step or third-2 step, and the fourth step, and the substance obtained in the third-3 step is used instead of the precursor (B) in the fourth step:

Third-3 Step:

a step of heating the precursor (B) obtained in the third step, or the acid-treated precursor (B) obtained in the third-2 step, in the presence of a swelling agent so as to swell the layered precursor, to thereby modify the state of the superposition thereof.

12. (currently amended): The process for producing the titanosilicate according to claim 8 ~~any one of claims 8 to 11~~, wherein the template compound is a nitrogen-containing compound.

13. (original): The process for producing the titanosilicate according to claim 12, wherein the nitrogen-containing compound is amine and/or quaternary ammonium compound.

14. (original): The process for producing the zeolite substance according to claim 12, wherein the nitrogen-containing compound is at least one member selected from the group consisting of piperidine, hexamethyleneimine and a mixture thereof.

15. The process for producing the titanosilicate according to claim 8~~any one of claims 8 to 14~~, wherein the boron-containing compound is at least one member selected from the group consisting of boric acid, borate, boron oxide, boron halide and trialkylborons.

16. (currently amended): The process for producing the titanosilicate according to claim 8~~any one of claims 8 to 15~~, wherein the silicon-containing compound is at least one member selected from the group consisting of silicic acid, silicate, silicon oxide, silicon halide, fumed silicas, tetraalkyl orthosilicates and colloidal silica.

17. (currently amended): The process for producing the titanosilicate according to claim 8~~any one of claims 8 to 16~~, wherein the ratio of boron to silicon in the mixture at the first step is, in terms of the molar ratio, boron : silicon = 0.01 to 10 : 1.

18. (currently amended): The process for producing the titanosilicate according to claim 8~~any one of claims 8 to 17~~, wherein the ratio of boron to silicon in the mixture at the first step is, in terms of the molar ratio, boron : silicon = 0.05 to 10 : 1.

19. (currently amended): The process for producing the titanosilicate according to claim 8~~any one of claims 8 to 18~~, wherein the ratio of water to silicon in the mixture at the first step is, in terms of the molar ratio: water : silicon = 5 to 200 : 1.

20. (currently amended): The process for producing the titanosilicate according to claim 8~~any one of claims 8 to 19~~, wherein the ratio of template compound to silicon in the mixture.

21. (currently amended): The process for producing the titanosilicate according to claim 8~~any one of claims 8 to 19~~, wherein the heating temperature in the first step is from 110 to 200°C.

22. (currently amended): The process for producing the titanosilicate according to claim 8~~any one of claims 8 to 20~~, wherein the acid used for the acid-treatment in the second step is a nitric acid or a sulfuric acid.

23. (currently amended): The process for producing the titanosilicate according to claim 8~~any one of claims 8 to 22~~, wherein the heating temperature in the third step is from 110 to 200°C.

24. (currently amended): The process for producing the titanosilicate according to claim 8~~any one of claims 8 to 23~~, wherein the calcination temperature in the fourth step is from 200 to 700°C.

25. (currently amended): The process for producing the titanosilicate according to claim 9~~any one of claims 9 to 24~~, wherein the calcination temperature in the first-2 step is from 200 to 700°C.

26. (currently amended): The process for producing the titanosilicate according to claim 8~~any one of claims 8 to 25~~, wherein in the third step, the acid-treated precursor (A) obtained in the second step and the mixture containing a template compound, a titanium-containing compound and water are previously mixed and then heated.

27. (currently amended): The process for producing the titanosilicate according to claim 8~~any one of claims 8 to 26~~, wherein in the third step, the acid-treated precursor (A) is treated by a dry gel method such that a mixture containing the acid-treated precursor (A) obtained in the second step, a titanium-containing compound and water and a mixture containing a template compound and water are charged separately, the vapor of the containing a template compound and water is caused to contact the mixture containing the titanium-containing compound and the acid-treated precursor (A).

28. (currently amended): A process for producing an oxidized compound, comprising performing an oxidation reaction of an organic compound using the oxidizing agent in the presence of the titanosilicate described in claim 1~~any one of claims 1 to 7~~.

29. (original): The process for producing an oxidized compound according to claim 28, wherein the oxidizing agent is oxygen or peroxide.

30. (original): The process for producing an oxidized compound according to claim 29, wherein the peroxide is at least one compound selected from the group consisting of hydrogen peroxide, tert-butyl hydroperoxide, tert-amyl hydroperoxide, cumene hydroperoxide, ethylbenzene hydroperoxide, cyclohexyl hydroperoxide, methylcyclohexyl hydroperoxide, tetralin hydroperoxide, isobutylbenzene hydroperoxide, ethylnaphthalene hydroperoxide and peracetic acid.

31. The process for producing an oxidized compound according to claim 26~~any one of claims 26 to 30~~, wherein the oxidation reaction is performed in the presence of at least one solvent selected from the group consisting of alcohols, ketones, nitriles and water.

32. (currently amended): The process for producing an oxidized compound according to claim 26~~any one of claims 26 to 32~~ wherein the oxidation reaction of an organic compound is an oxidation reaction of a carbon-carbon double bond.

33. (currently amended): The process for producing an oxidized compound according to claim 26~~any one of claims 26 to 32~~, wherein the oxidation reaction of an organic compound is an epoxidation reaction or a dioliation reaction.

34. (currently amended): The process for producing an oxidized compound according to claim 26~~any one of claims 26 to 31~~, wherein the oxidation reaction of an organic compound is an ammoximation.